

PMBFJ108; PMBFJ109; PMBFJ110

N-channel junction FETs

Rev. 03 — 4 August 2004

Product data sheet

1. Product profile

1.1 General description

Symmetrical N-channel junction FETs in a SOT23 package.

1.2 Features

- High-speed switching
- Interchangeability of drain and source connections
- Low R_{DSon} at zero gate voltage (< 8 Ω for PMBFJ108).

1.3 Applications

- Analog switches
- Choppers and commutators
- Audio amplifiers.

2. Pinning information

Table 1: Pinning

Pin	Description [1]	Simplified outline	Symbol
1	drain		
2	source		
3	gate	1 2 SOT23	3 → 1 2 sym053

[1] Drain and source are interchangeable.







3. Ordering information

Table 2: Ordering information

Type number	Package				
	Name	Description	Version		
PMBFJ108	-	plastic surface mounted package; 3 leads	SOT23		
PMBFJ109	_				
PMBFJ110	_				

4. Marking

Table 3: Marking

Type number	Marking code [1]
PMBFJ108	38*
PMBFJ109	39*
PMBFJ110	40*

^{[1] * =} p: Made in Hong Kong

5. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	±25	V
V_{GSO}	gate-source voltage		-	-25	V
V_{GDO}	gate-drain voltage		-	-25	V
I_{G}	forward gate current (DC)		-	50	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	<u>[1]</u> _	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

^[1] Mounted on an FR4 printed-circuit board.

6. Thermal characteristics

Table 5: Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		<u>11</u> 500	K/W

^[1] Mounted on an FR4 printed-circuit board.

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^{* =} t: Made in Malaysia

^{* =} W: Made in China



7. Static characteristics

Table 6: Static characteristics

 $T_i = 25 \,^{\circ}C$.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate-source leakage current	$V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	-3	nΑ
I _{DSX}	drain-source cut-off current	$V_{GS} = -10 \text{ V}; V_{DS} = 5 \text{ V}$	-	-	3	nΑ
I _{DSS}	drain-source leakage current					
	PMBFJ108	V _{GS} = 0 V; V _{DS} = 15 V	80	-	-	mΑ
	PMBFJ109	V _{GS} = 0 V; V _{DS} = 15 V	40	-	-	mΑ
	PMBFJ110	V _{GS} = 0 V; V _{DS} = 15 V	10	-	-	mΑ
V _{(BR)GSS}	gate-source breakdown voltage	$I_G = -1 \mu A; V_{DS} = 0 V$	-	-	-25	V
V_{GSoff}	gate-source cut-off voltage					
	PMBFJ108	$I_D = 1 \mu A; V_{DS} = 5 V$	-10	-	-3	V
	PMBFJ109	$I_D = 1 \mu A; V_{DS} = 5 V$	-6	-	-2	V
	PMBFJ110	$I_D = 1 \mu A; V_{DS} = 5 V$	-4	-	-0.5	V
R _{DSon}	drain-source on-state resistance					
	PMBFJ108	V _{GS} = 0 V; V _{DS} = 0.1 V	-	-	8	Ω
	PMBFJ109	V _{GS} = 0 V; V _{DS} = 0.1 V	-	-	12	Ω
	PMBFJ110	V _{GS} = 0 V; V _{DS} = 0.1 V	-	-	18	Ω

8. Dynamic characteristics

Table 7: Dynamic characteristics

 $T_j = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; f = 1 \text{ MHz}$		-	15	30	pF
		V_{DS} = 0 V; V_{GS} = 0 V; f = 1 MHz; T_{amb} = 25 °C		-	50	85	pF
C _{rss}	feedback capacitance	$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; f = 1 \text{ MHz}$		-	8	15	pF
Switching	g times (see Figure 2)						
t _d	delay time		[1]	-	2	-	ns
t _{on}	turn-on time		<u>[1]</u>	-	4	-	ns
ts	storage time		<u>[1]</u>	-	4	-	ns
t _{off}	turn-off time		<u>[1]</u>	-	6	-	ns

^[1] Test conditions for switching times are as follows:

 V_{DD} = 1.5 V, V_{GS} = 0 V to V_{GSoff} (all types);

 V_{GSoff} = -12 V, R_L = 100 Ω (PMBFJ108);

 $V_{GSoff} = -7 \text{ V}, R_L = 100 \Omega \text{ (PMBFJ109)};$

 V_{GSoff} = -5 V, R_L = 100 Ω (PMBFJ110).

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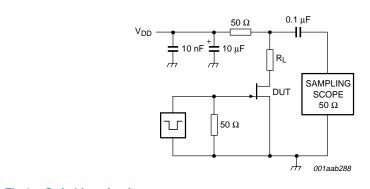


Fig 1. Switching circuit.

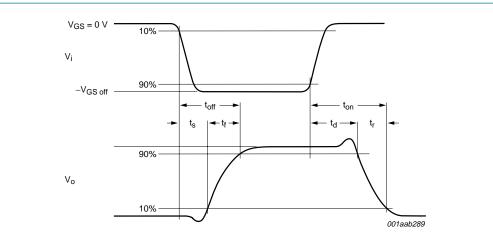


Fig 2. Input and output waveforms.



9. Package outline

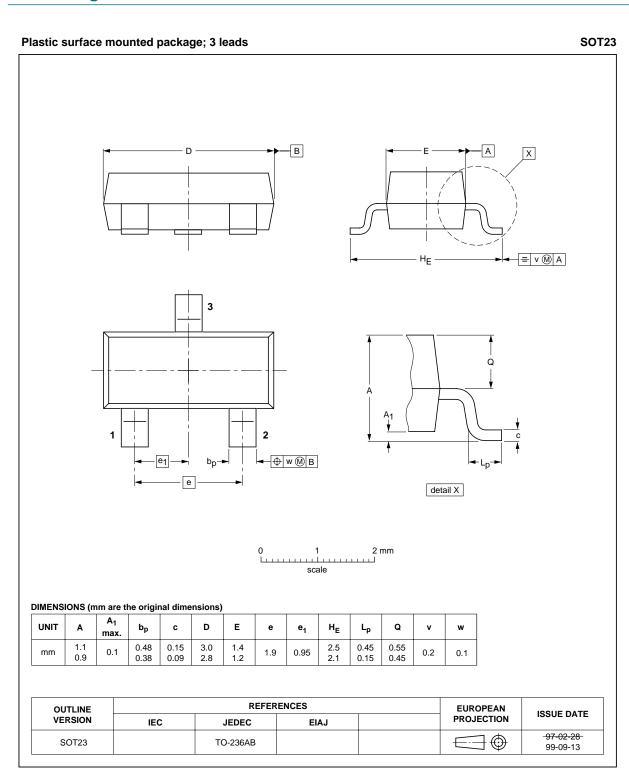


Fig 3. Package outline.

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10. Revision history

Table 8: Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
PMBFJ108_109_110_ 3	20040804	Product data sheet	-	9397 750 13401	PMBFJ108_109_110_ CNV_2
Modifications:	 The format of this data sheet has been redesigned to comply with the new presentation information standard of Philips Semiconductors. 				e new presentation and
	Table 3 "N	<mark>larking"</mark> : Added new m	arking code.		
PMBFJ108_109_110_ CNV_2	19971201	Product specification	-	not applicable	-

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11. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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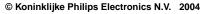
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